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(54) Title: A MONOLITHIC INTEGRATED STRUCTURE COMPRISING A BURIED HETEROSTRUCTURE SEMICONDUCTOR OPTICAL AMPLIFIER AND A PHOTODETECTOR

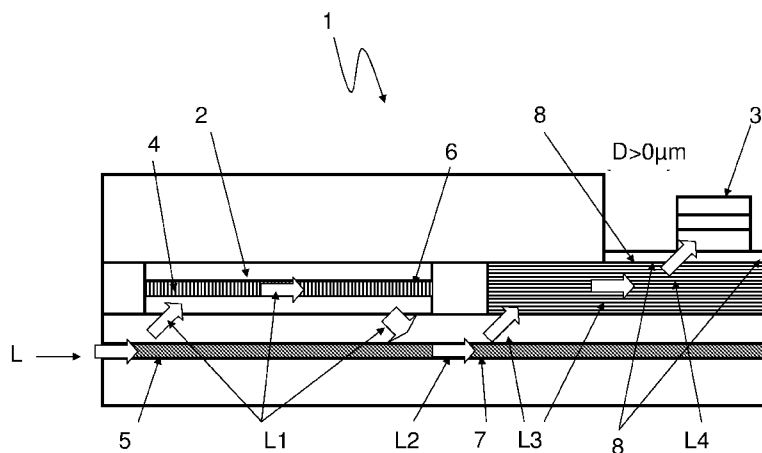


Fig. 2

(57) Abstract: A monolithic integrated structure comprising a buried heterostructure semiconductor optical amplifier (2) and a deep ridge optical receiver comprising such structure are disclosed.